AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) An integrated circuit comprising:

a semiconductor substrate;

an epitaxial layer coupled to the substrate, the epitaxial layer having been coupled to the substrate via a transfer process comprising:

doping the epitaxial layer with a first quantity of a first ionic material and a second quantity of a second ionic material;

annealing the epitaxial layer and semiconductor substrate at a first annealing temperature, wherein the first annealing temperature is between approximately 439C and approximately 451C.

2. (Original) The integrated circuit of claim 1 wherein the sum of the first quantity of the first ionic material and the second quantity of the second ionic material is no greater than approximately $2x10^{16}$ cm^{-2}.

3. (Canceled)

4. (Original) The integrated circuit of claim 1 wherein the first annealing temperature is between approximately 419C and approximately 430C.

5. (Original) The integrated circuit of claim 4 wherein the process further comprises mechanically separating a donor wafer, comprising the epitaxial layer, from a handle wafer, comprising the semiconductor substrate.

6. (Original) The integrated circuit of claim 2 wherein the second ionic material comprises hydrogen ions to react with the epitaxial layer at an energy level of approximately 40 KeV.

7. (Original) The integrated circuit of claim 6 wherein the first ionic material comprises helium ions to react with the epitaxial layer at an energy level of approximately 50 KeV.

8. (Original) The integrated circuit of claim 7 wherein the first quantity of helium ions is approximately $1x10^{16}$ cm^{-2} and the second quantity of hydrogen ions is approximately $1x10^{16}$ cm^{-2}.

9.-35. (Canceled)